

QS5U16

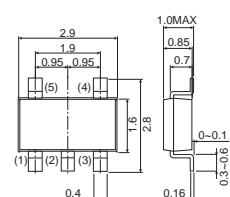
Silicon N-channel MOSFET
Schottky Barrier DIODE

- 1) The Q5SU16 combines Nch MOSFET with a Schottky barrier diode in a single TSMT5 package.
- 2) Low on-state resistance with fast switching.
- 3) Low voltage drive (2.5V).
- 4) The Independently connected Schottky barrier diode has low forward voltage.

Load switch, DC / DC conversion

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
QS5U16		○

TSMT5



Each lead has same dimensions
Abbreviated symbol : U16

The diagram shows a MOSFET symbol with an ESD protection diode (*1) connected between the gate and source, and a body diode (*2) connected between the drain and source. The pins are labeled (1) through (5).

- (1) Gate
- (2) Source
- (3) Anode
- (4) Cathode
- (5) Drain

*1 ESD PROTECTION DIODE
*2 BODY DIODE

Transistors

●Absolute maximum ratings (Ta=25°C)

<MOSFET>

Parameter	Symbol	Limits	Unit
Drain-source voltage	V _{DSS}	30	V
Gate-source voltage	V _{GSS}	12	V
Drain current	Continuous	I _D	±2.0
	Pulsed	I _{DP} *1	±8.0
Source current (Body diode)	Continuous	I _S	0.8
	Pulsed	I _{SP} *1	3.2
Channel temperature	T _{ch}	150	°C
Power dissipation	P _D *3	0.9	W/ELEMENT

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Repetitive peak reverse voltage	V _{RM}	30	V
Reverse voltage	V _R	20	V
Forward current	I _F	0.5	A
Forward current surge peak	I _{FSM} *2	2.0	A
Junction temperature	T _j	150	°C
Power dissipation	P _D *3	0.7	W/ELEMENT

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Total power dissipation	P _D *3	1.25	W / TOTAL
Range of Storage temperature	T _{stg}	-55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1% *2 60Hz-1cyc. *3 Mounted on a ceramic board

●Electrical characteristics (Ta=25°C)

<MOSFET>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	—	—	10	μA	V _{GS} =12V / V _{DS} =0V
Drain-source breakdown voltage	V _{(BR) DSS}	30	—	—	V	I _D =1mA, / V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	—	—	1	μA	V _{DS} =30V / V _{GS} =0V
Gate threshold voltage	V _{GS(th)}	0.5	—	1.5	V	V _{DS} =10V / I _D =1mA
Static drain-source on-state resistance	R _{DS(on)} *	—	71	100	mΩ	I _D =2.0A, V _{GS} =4.5V
		—	76	107	mΩ	I _D =2.0A, V _{GS} =4V
		—	110	154	mΩ	I _D =2.0A, V _{GS} =2.5V
Forward transfer admittance	Y _{fs} *	1.5	—	—	S	V _{DS} =10V, I _D =2.0A
Input capacitance	C _{iss}	—	175	—	pF	V _{DS} =10V
Output capacitance	C _{oss}	—	50	—	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	—	25	—	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	—	8	—	ns	I _D =1.0A
Rise time	t _r *	—	10	—	ns	V _{DD} =15V
Turn-off delay time	t _{d(off)} *	—	21	—	ns	V _{GS} =4.5V
Fall time	t _f *	—	8	—	ns	R _L =15Ω
Total gate charge	Q _g *	—	2.8	3.9	nC	R _G =10Ω
Gate-source charge	Q _{gs} *	—	0.6	—	nC	V _{DD} =15V
Gate-drain charge	Q _{gd} *	—	0.8	—	nC	V _{GS} =4.5V

*Pulsed

<Body diode (source-drain)>

Forward voltage	V _{SD} *	—	—	1.2	V	I _S =3.2A / V _{GS} =0V
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* Pulsed

<Di>

Forward voltage	V _F	—	—	0.36	V	I _F =0.1A
		—	—	0.47	V	I _F =0.5A
Reverse current	I _R	—	—	100	μA	V _R =20V

Transistors

●Electrical characteristic curves

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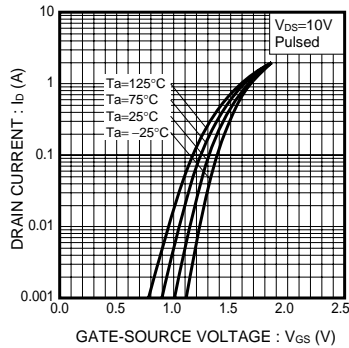


Fig.1 Typical Transfer Characteristics

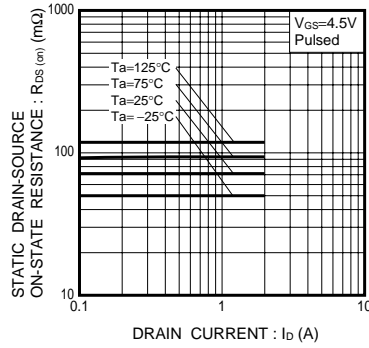


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

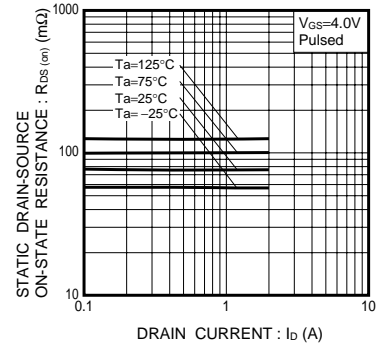


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

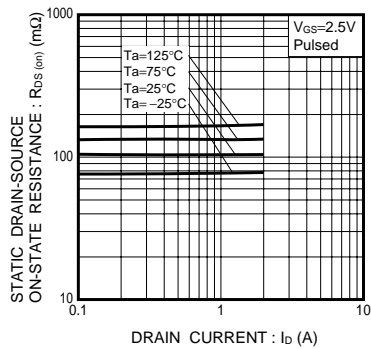


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

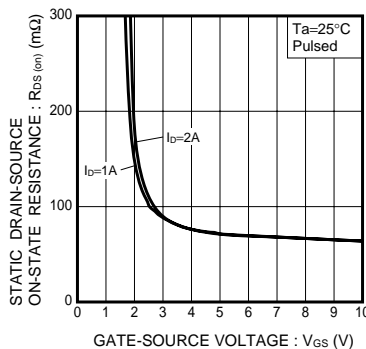


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

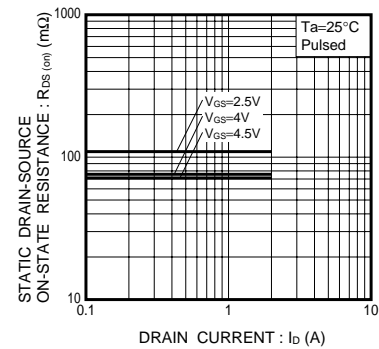


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

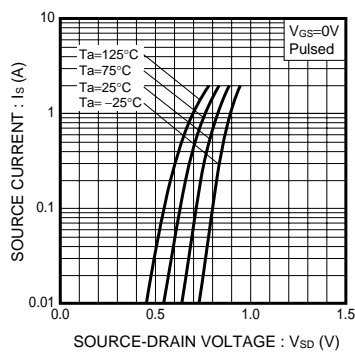


Fig.7 Reverse Drain Current vs. Source-Drain Current

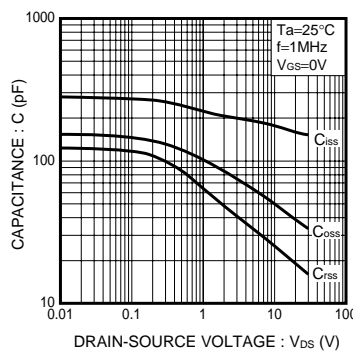


Fig.8 Typical Capacitance vs. Drain-Source Voltage

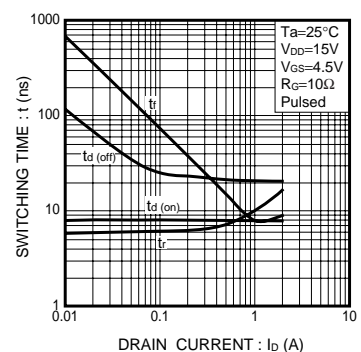


Fig.9 Switching Characteristics

Transistors

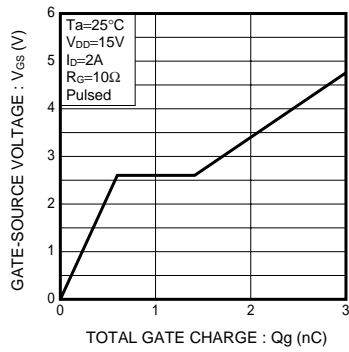


Fig.10 Dynamic Input Characteristics

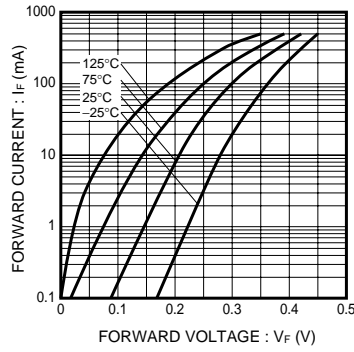


Fig.11 Forward Current vs. Forward Voltage

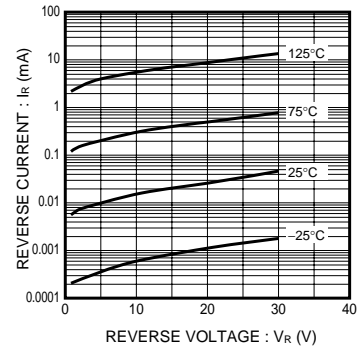


Fig.12 Reverse Current vs. Reverse Voltage

●Measurement circuits

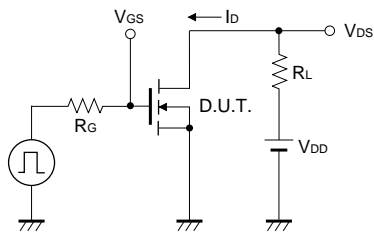


Fig.13 Switching Time Measurement Circuit

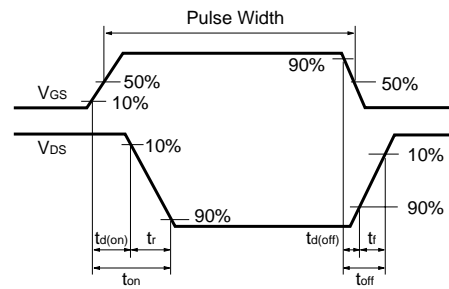


Fig.14 Switching Waveforms

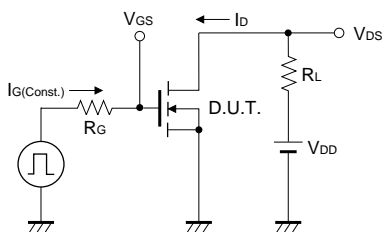


Fig.15 Gate Charge Measurement Circuit

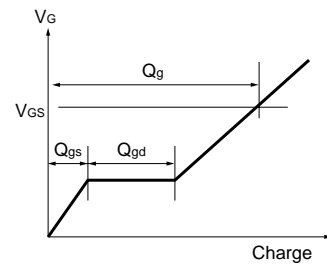


Fig.16 Gate Charge Waveform

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